TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type ( $\pi$ -MOSVI)

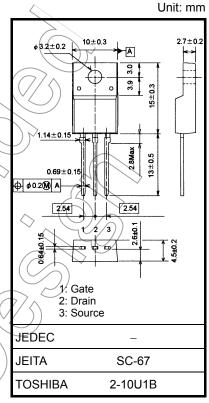
# 2SK3757

#### **Switching Regulator Applications**

- Low drain-source ON resistance:  $R_{DS}(ON) = 1.9 \Omega$  (typ.)
- High forward transfer admittance: |Y<sub>fs</sub>| = 1.0 S (typ.)
- Low leakage current: I<sub>DSS</sub> = 100 μA (max) (V<sub>DS</sub> = 450 V)
- Enhancement model:  $V_{th}$  = 2.0 to 4.0 V ( $V_{DS}$  = 10 V,  $I_{D}$  = 1 mA)

### Absolute Maximum Ratings (Ta = 25°C)

| Characteristic                                       |                                     |          | Symbol           | Rating  | Unit                  |
|--|-------------------------------------|----------|------------------|---------|-----------------------|
| Drain-source voltage                                 |                                     |          | $V_{DSS}$        | 450     | $(\mathcal{N} \land)$ |
| Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ ) |                                     |          | $V_{DGR}$        | 450     | V                     |
| Gate-source voltage                                  |                                     |          | $V_{GSS}$        | ±30     | V                     |
| Drain current  | DC                                  | (Note 1) | ΙD               | 2       | A                     |
|  | Pulse                               | (Note 1) | $I_{DP}$         | 5       | V A                   |
| Drain power dissipat                                 | Drain power dissipation (Tc = 25°C) |          |                  | 30      | W                     |
| Single pulse avalanche energy (Note 2)               |                                     |          | E <sub>AR</sub>  | 103     | mJ                    |
| Avalanche current                                    |                                     |          | IAR              | 2       | A                     |
| Repetitive avalanche energy (Note 3)                 |                                     |          | EAR              | )) 3    | mJ                    |
| Channel temperature                                  |                                     |          | Tch              | 150     | ∕ °C                  |
| Storage temperature range                            |                                     |          | T <sub>stg</sub> | -55~150 | <i>J</i> ,¢           |



Weight: 1.7 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Thermal Characteristics**

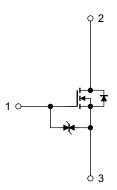
| Characteristic                                  | ol Max   | Unit |
|---|----------|------|
| Thermal resistance, channel to case Rth (ch.    | -c) 4.17 | °C/W |
| Thermal resistance, channel to ambient Rth (ch. | -a) 62.5 | °C/W |

Note 1: Ensure that the channel temperature does not exceed 150°C during use of the device.

Note 2:  $V_{DD} = 90~V,~T_{ch} = 25^{\circ}C$  (initial), L = 42.8 mH, R<sub>G</sub> = 25  $\Omega,~I_{AR} = 2~A$ 

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Handle with caution.

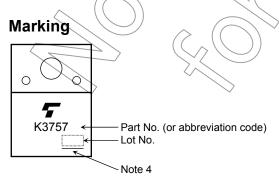


#### **Electrical Characteristics (Ta = 25°C)**

| Characteristic                 |                      | Symbol               | Test Condition  | Min                     | Тур.  | Max                       | Unit |
|--------------------------------|----------------------|----------------------|---|-------------------------|-------|---------------------------|------|
| Gate leakage current           |                      | I <sub>GSS</sub>     | $V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$                       | _                       | _     | ±10                       | μА   |
| Gate -source brea              | kdown voltage        | V (BR) GSS           | $I_G = \pm 10 \ \mu A, \ V_{DS} = 0 \ V$                                | ±30                     | _     | _                         | V    |
| Drain cutoff currer            | Drain cutoff current |                      | V <sub>DS</sub> = 450 V, V <sub>GS</sub> = 0 V                          |                         | _     | 100                       | μА   |
| Drain-source breakdown voltage |                      | V (BR) DSS           | $I_D = 10$ mA, $V_{GS} = 0$ V   | 450                     | _     | _                         | V    |
| Gate threshold voltage         |                      | V <sub>th</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA                           | 2.0                     | ) / _ | 4.0                       | V    |
| Drain-source ON resistance     |                      | R <sub>DS</sub> (ON) | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 1 A                            | > <u>~</u>              | 1.9   | 2.45                      | Ω    |
| Forward transfer a             | dmittance            | Y <sub>fs</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 A                            | 0.28                    | 1.0   | _                         | S    |
| Input capacitance              |                      | C <sub>iss</sub>     |   | _                       | 330   | _                         |      |
| Reverse transfer capacitance   |                      | C <sub>rss</sub>     | V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz                | _                       | 4     | _                         | pF   |
| Output capacitance             |                      | Coss                 |   | _                       | 45    |                           |      |
| Switching time                 | Rise time            | t <sub>r</sub>       | V <sub>GS</sub> D=1A V <sub>OUT</sub>                                   | - (                     | 15    | <i>&gt;</i>   <i>&gt;</i> |      |
|                                | Turn-on time         | ton                  | 0 V   |                         | 25    | ) _                       |      |
|                                | Fall time            | t <sub>f</sub>       | V <sub>DD</sub> ≈ 200 V   | $\widehat{\mathcal{D}}$ | 20    | _                         | ns   |
|                                | Turn-off time        | t <sub>off</sub>     | Duty ≤ 1%, t <sub>W</sub> = 10 μs                                       | ) —                     | 80    | _                         |      |
| Total gate charge              |                      | Qg                   |   | _                       | 9     | _                         |      |
| Gate-source charge             |                      | Q <sub>g\$</sub>     | $V_{DD} \simeq 360 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 2 \text{ A}$ | _                       | 5     | _                         | nC   |
| Gate-drain charge              |                      | Qgd                  |   | _                       | 4     | _                         |      |

## Source-Drain Ratings and Characteristics (Ta = 25°C)

| Characteristic                            | Symbol          | Test Condition                                | Min | Тур. | Max  | Unit |  |  |
|---|-----------------|---|-----|------|------|------|--|--|
| Continuous drain reverse current (Note 1) | I <sub>DR</sub> |   | _   | _    | 2    | Α    |  |  |
| Pulse drain reverse current (Note 1)      | IDRP            |   | _   | _    | 5    | Α    |  |  |
| Forward voltage (diode)                   | VDSF            | I <sub>DR</sub> = 2 A, V <sub>GS</sub> = 0 V  | _   | _    | -1.5 | ٧    |  |  |
| Reverse recovery time                     | t <sub>rr</sub> | $I_{DR} = 2 \text{ A}, V_{GS} = 0 \text{ V},$ | _   | 1000 | _    | ns   |  |  |
| Reverse recovery charge                   | Q <sub>rr</sub> | dI <sub>DR</sub> /dt = 100 A/μs               |     | 5.0  |      | μС   |  |  |

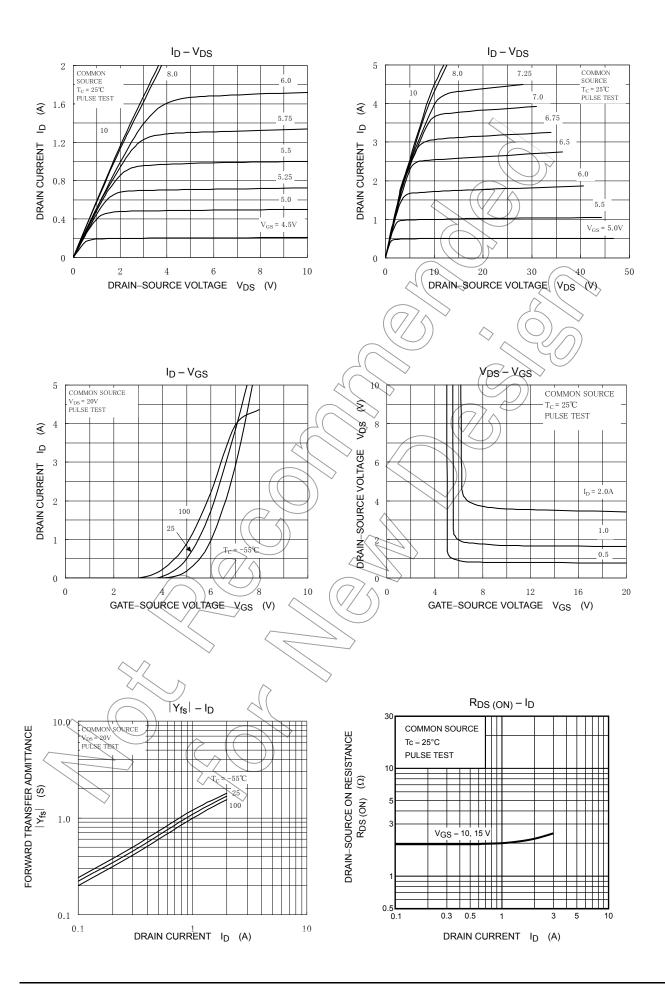


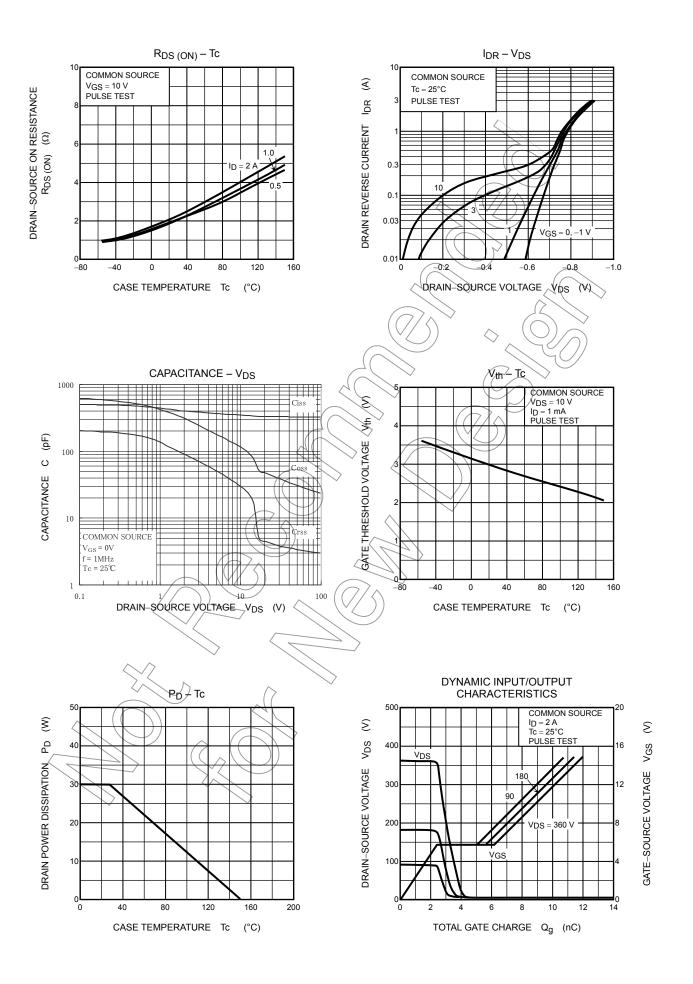
Note 4: A line under a Lot No. identifies the indication of product Labels.

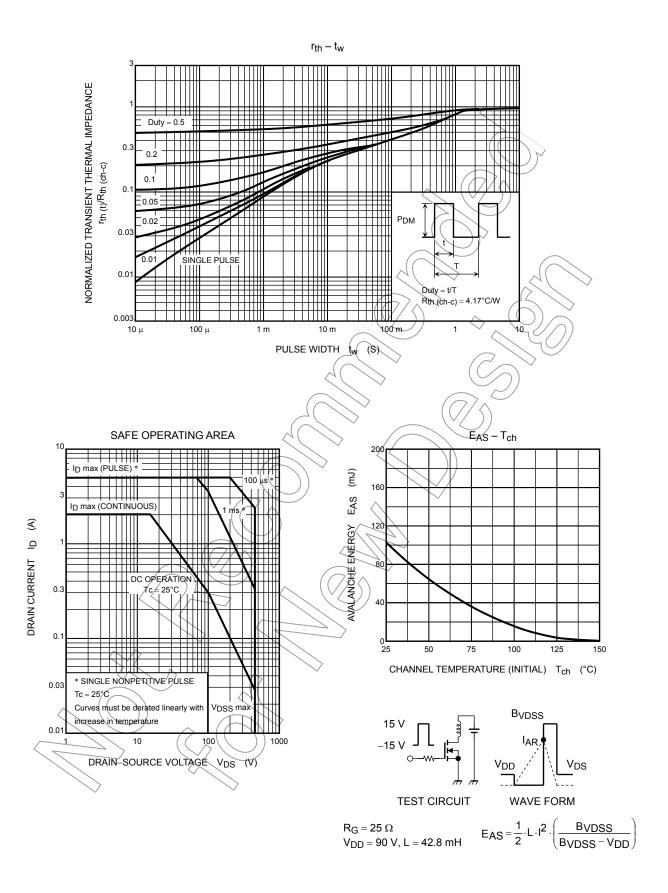
Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

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